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Understanding Embedded - Microprocessors

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Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8349zuajd

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Electrical Characteristics

- Dual industry-standard I²C interfaces
 - Two-wire interface
 - Multiple master support
 - Master or slave I²C mode support
 - On-chip digital filtering rejects spikes on the bus
 - System initialization data optionally loaded from I²C-1 EPROM by boot sequencer embedded hardware
- DMA controller
 - Four independent virtual channels
 - Concurrent execution across multiple channels with programmable bandwidth control
 - Handshaking (external control) signals for all channels: DMA_DREQ[0:3],
 DMA_DACK[0:3], DMA_DDONE[0:3]
 - All channels accessible to local core and remote PCI masters
 - Misaligned transfer capability
 - Data chaining and direct mode
 - Interrupt on completed segment and chain
- DUART
 - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Serial peripheral interface (SPI) for master or slave
- General-purpose parallel I/O (GPIO)
 - 64 parallel I/O pins multiplexed on various chip interfaces
- System timers
 - Periodic interrupt timer
 - Real-time clock
 - Software watchdog timer
 - Eight general-purpose timers
- Designed to comply with IEEE Std. 1149.1TM, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8349EA. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 **Overall DC Electrical Characteristics**

This section covers the ratings, conditions, and other characteristics.

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8349EA for the 3.3-V signals, respectively.

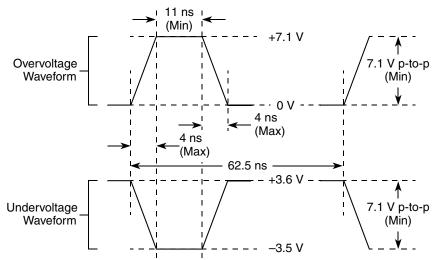


Figure 3. Maximum AC Waveforms on PCI Interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	40	OV _{DD} = 3.3 V
PCI signals (not including PCI output clocks)	25	
PCI output clocks (including PCI_SYNC_OUT)	40	
DDR signal	18	GV _{DD} = 2.5 V
DDR2 signal	18 36 (half-strength mode)	GV _{DD} = 1.8 V
TSEC/10/100 signals	40	LV _{DD} = 2.5/3.3 V
DUART, system control, I ² C, JTAG, USB	40	OV _{DD} = 3.3 V
GPIO signals	40	OV _{DD} = 3.3 V, LV _{DD} = 2.5/3.3 V

Table 3. Output Drive Capability

2.2 **Power Sequencing**

This section details the power sequencing considerations for the MPC8349EA.

2.2.1 Power-Up Sequencing

MPC8349EA does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD} , LV_{DD} , and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power

Power Characteristics

supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD} , LV_{DD} , and OV_{DD}) and assert PORESET before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

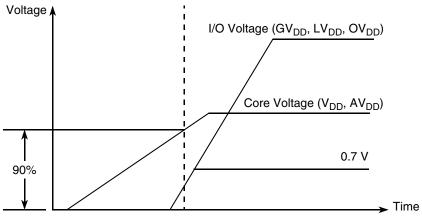


Figure 4. Power Sequencing Example

I/O voltage supplies (GV_{DD} , LV_{DD} , and OV_{DD}) do not have any ordering requirements with respect to one another.

3 Power Characteristics

The estimated typical power dissipation for the MPC8349EA device is shown in Table 4.

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at T _J = 65	Typical ^{2, 3}	Maximum ⁴	Unit
TBGA	333	333	2.0	3.0	3.2	W
		166	1.8	2.8	2.9	W
	400	266	2.1	3.0	3.3	W
		133	1.9	2.9	3.1	W
	450	300	2.3	3.2	3.5	W
		150	2.1	3.0	3.2	W
	500	333	2.4	3.3	3.6	W
		166	2.2	3.1	3.4	W
	533	266	2.4	3.3	3.6	W
		133	2.2	3.1	3.4	W
	667 ^{5, 6}	333	3.5	4.6	5	W

 Table 4. MPC8349EA Power Dissipation¹

¹ The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 5.

DDR and DDR2 SDRAM

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Output low current (V _{OUT} = 0.280 V)I OL13.4mA
--

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

2. MV_{REF} is expected to equal 0.5 × GV_{DD} , and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.

 V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

Table 13 provides the DDR2 capacitance when $GV_{DD}(typ) = 1.8$ V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, DQS	C _{DIO}	_	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, f = 1 MHz, T_A = 25°C, V_{OUT} = $GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR SDRAM component(s) when $GV_{DD}(typ) = 2.5 \text{ V}.$

Table 14. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
I/O supply voltage	GV _{DD}	2.375	2.625	V	1
I/O reference voltage	MV _{REF}	$0.49 imes GV_{DD}$	$0.51 imes GV_{DD}$	V	2
I/O termination voltage	V _{TT}	MV _{REF} – 0.04	MV _{REF} + 0.04	V	3
Input high voltage	V _{IH}	MV _{REF} + 0.18	GV _{DD} + 0.3	V	—
Input low voltage	V _{IL}	-0.3	MV _{REF} – 0.18	V	—
Output leakage current	I _{OZ}	-9.9	-9.9	μA	4
Output high current (V _{OUT} = 1.95 V)	I _{OH}	-15.2	—	mA	—
Output low current (V _{OUT} = 0.35 V)	I _{OL}	15.2	_	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

DDR and DDR2 SDRAM

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) \pm 5%.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
MDQS epilogue end	t _{DDKHME}	-0.6	0.6	ns	6

Notes:

- The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output goes invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are set up (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
 </sub>
- 2. All MCK/ \overline{MCK} referenced measurements are made from the crossing of the two signals ±0.1 V.
- 3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
- 4. t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register and is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters are set to the same adjustment value. See the MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual for the timing modifications enabled by use of these bits.
- 5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside the data eye at the pins of the microprocessor.
- 6. All outputs are referenced to the rising edge of MCK(n) at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 6 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

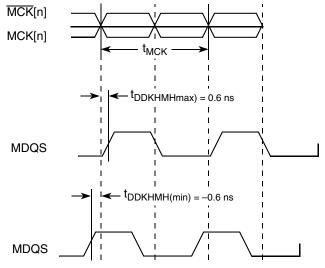


Figure 6. Timing Diagram for t_{DDKHMH}

Ethernet: Three-Speed Ethernet, MII Management

Table 27. MII Transmit AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
TX_CLK data clock rise (20%-80%)	t _{MTXR}	1.0	_	4.0	ns
TX_CLK data clock fall (80%-20%)	t _{MTXF}	1.0		4.0	ns

Note:

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub></sub>

Figure 11 shows the MII transmit AC timing diagram.

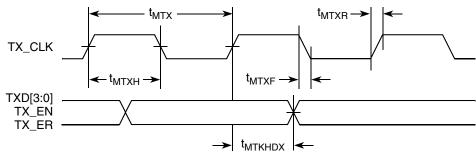


Figure 11. MII Transmit AC Timing Diagram

8.2.2.2 MII Receive AC Timing Specifications

Table 28 provides the MII receive AC timing specifications.

Table 28. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RX_CLK clock period 10 Mbps	t _{MRX}	_	400	—	ns
RX_CLK clock period 100 Mbps	t _{MRX}	_	40	_	ns
RX_CLK duty cycle	t _{MRXH} /t _{MRX}	35	_	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t _{MRDVKH}	10.0	_	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t _{MRDXKH}	10.0		—	ns

Table 28. MII Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RX_CLK clock rise (20%–80%)	t _{MRXR}	1.0	_	4.0	ns
RX_CLK clock fall time (80%–20%)	t _{MRXF}	1.0	_	4.0	ns

Note:

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub>

Figure 12 provides the AC test load for TSEC.

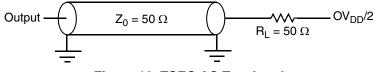


Figure 12. TSEC AC Test Load

Figure 13 shows the MII receive AC timing diagram.

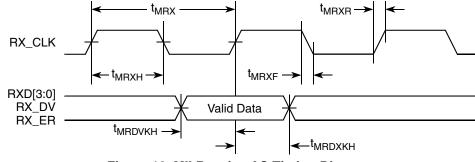


Figure 13. MII Receive AC Timing Diagram

8.2.3 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

Table 30. TBI Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) setup time to rising PMA_RX_CLK	t _{TRDVKH} ²	2.5	—	—	ns
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) hold time to rising PMA_RX_CLK	t _{TRDXKH} ²	1.5	—	—	ns
RX_CLK clock rise time (20%–80%)	t _{TRXR}	0.7	—	2.4	ns
RX_CLK clock fall time (80%–20%)	t _{TRXF}	0.7	—	2.4	ns

Notes:

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript SK followed by the clock that is being skewed (TRX).
</sub>

2. Setup and hold time of even numbered RCG are measured from the riding edge of PMA_RX_CLK1. Setup and hold times of odd-numbered RCG are measured from the riding edge of PMA_RX_CLK0.

Figure 15 shows the TBI receive AC timing diagram.

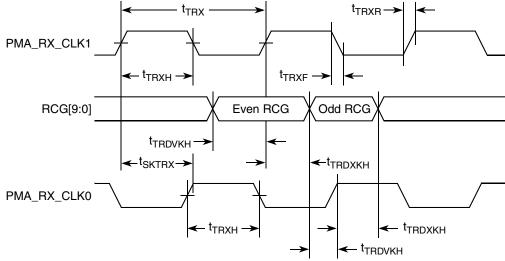


Figure 15. TBI Receive AC Timing Diagram

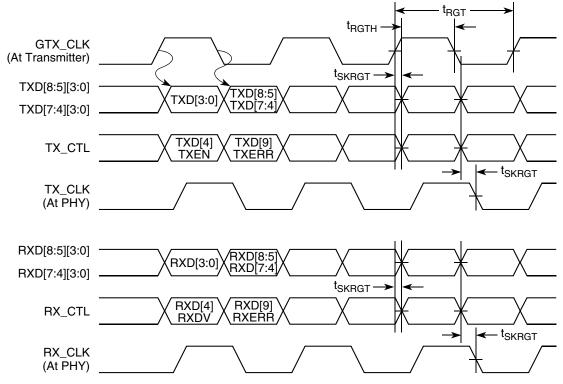


Figure 16 shows the RBMII and RTBI AC timing and multiplexing diagrams.

Figure 16. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to the MII management interface signals management data input/output (MDIO) and management data clock (MDC). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 2.5 or 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 32 and Table 33.

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (2.5 V)	LV _{DD}	—		2.37	2.63	V
Output high voltage	V _{OH}	$I_{OH} = -1.0 \text{ mA}$	$LV_{DD} = Min$	2.00	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	I _{OL} = 1.0 mA	$LV_{DD} = Min$	GND – 0.3	0.40	V
Input high voltage	V _{IH}	—	$LV_{DD} = Min$	1.7	—	V
Input low voltage	V _{IL}	—	$LV_{DD} = Min$	-0.3	0.70	V

Local Bus

Figure 21 through Figure 26 show the local bus signals.

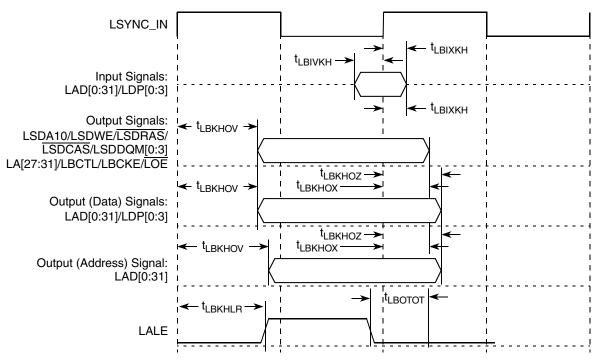


Figure 21. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

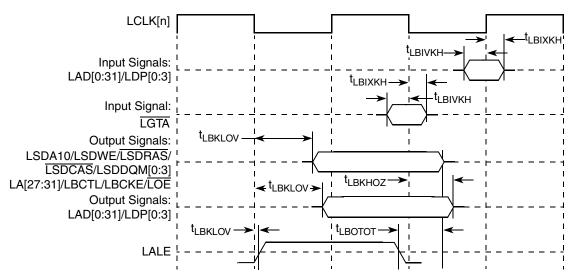


Figure 22. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

Table 45. PCI AC Timing Specifications at 66 MHz ¹ ((continued)
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Parameter	Symbol ²	Min	Max	Unit	Notes
PORESET to REQ64 hold time	t _{PCRHRX}	0	50	ns	6

Notes:

- 1. PCI timing depends on M66EN and the ratio between PCI1/PCI2. Refer to the PCI chapter of the reference manual for a description of M66EN.
- 2. The symbols for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.}
- 3. See the timing measurement conditions in the PCI 2.3 Local Bus Specifications.
- 4. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 5. Input timings are measured at the pin.
- 6. The setup and hold time is with respect to the rising edge of PORESET.

Table 46 provides the PCI AC timing specifications at 33 MHz.

Table 46. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol ¹	Min	Мах	Unit	Notes
Clock to output valid	^t PCKHOV	—	11	ns	2
Output hold from clock	^t РСКНОХ	2	-	ns	2
Clock to output high impedance	^t рскноz	—	14	ns	2, 3
Input setup to clock	t _{PCIVKH}	3.0	_	ns	2, 4
Input hold from clock	t _{PCIXKH}	0	_	ns	2, 4
REQ64 to PORESET setup time	t _{PCRVRH}	5	_	clocks	5
PORESET to REQ64 hold time	t _{PCRHRX}	0	50	ns	5

Notes:

2. See the timing measurement conditions in the PCI 2.3 Local Bus Specifications.

3. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

4. Input timings are measured at the pin.

5. The setup and hold time is with respect to the rising edge of PORESET.

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
</sub>

SPI

17 SPI

This section describes the SPI DC and AC electrical specifications.

17.1 SPI DC Electrical Characteristics

Table 53 provides the SPI DC electrical characteristics.

Table 53. SPI DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Мах	Unit
Input high voltage	V _{IH}	_	2.0	OV _{DD} + 0.3	V
Input low voltage	V _{IL}	_	-0.3	0.8	V
Input current	I _{IN}	_	_	±5	μA
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

17.2 SPI AC Timing Specifications

Table 54 provides the SPI input and output AC timing specifications.

Table 54. SPI AC Timing Specifications¹

Parameter	Symbol ²	Min	Мах	Unit
SPI outputs valid—Master mode (internal clock) delay	t _{NIKHOV}	—	6	ns
SPI outputs hold—Master mode (internal clock) delay	t _{NIKHOX}	0.5	—	ns
SPI outputs valid—Slave mode (external clock) delay	t _{NEKHOV}	—	8	ns
SPI outputs hold—Slave mode (external clock) delay	t _{NEKHOX}	2	—	ns
SPI inputs—Master mode (internal clock input setup time	t _{NIIVKH}	4	—	ns
SPI inputs—Master mode (internal clock input hold time	t _{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t _{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t _{NEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50 percent level of the rising edge of CLKIN to the 50 percent level of the signal. Timings are measured at the pin.

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{NIKHOX} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).
</sub>

18.1 Package Parameters for the MPC8349EA TBGA

The package parameters are provided in the following list. The package type is $35 \text{ mm} \times 35 \text{ mm}$, 672 tape ball grid array (TBGA).

Package outline	35 mm × 35 mm
Interconnects	672
Pitch	1.00 mm
Module height (typical)	1.46 mm
Solder balls	62 Sn/36 Pb/2 Ag (ZU package) 96.5 Sn/3.5Ag (VV package)
Ball diameter (typical)	0.64 mm

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MBA[2]	H4	0	GV _{DD}	
MDIC0	AB1	I/O	—	9
MDIC1	AA1	I/O	—	9
	Local Bus Controller Interface			
LAD[0:31]	AM13, AP13, AL14, AM14, AN14, AP14, AK15, AJ15, AM15, AN15, AP15, AM16, AL16, AN16, AP16, AL17, AM17, AP17, AK17, AP18, AL18, AM18, AN18, AP19, AN19, AM19, AP20, AK19, AN20, AL20, AP21, AN21	I/O	OV _{DD}	_
LDP[0]/CKSTOP_OUT	AM21	I/O	OV _{DD}	—
LDP[1]/CKSTOP_IN	AP22	I/O	OV _{DD}	—
LDP[2]/LCS[4]	AN22	I/O	OV _{DD}	—
LDP[3]/LCS[5]	AM22	I/O	OV _{DD}	—
LA[27:31]	AK21, AP23, AN23, AP24, AK22	0	OV _{DD}	—
LCS[0:3]	AN24, AL23, AP25, AN25	0	OV _{DD}	—
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	AK23, AP26, AL24, AM25	0	OV _{DD}	—
LBCTL	AN26	0	OV _{DD}	—
LALE	AK24	0	OV _{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AP27	I/O	OV _{DD}	—
LGPL1/LSDWE/cfg_reset_source1	AL25	I/O	OV _{DD}	—
LGPL2/LSDRAS/LOE	AJ24	0	OV _{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	AN27	I/O	OV _{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	AP28	I/O	OV _{DD}	12
LGPL5/cfg_clkin_div	AL26	I/O	OV _{DD}	—
LCKE	AM27	0	OV _{DD}	—
LCLK[0:2]	AN28, AK26, AP29	0	OV _{DD}	—
LSYNC_OUT	AM12	0	OV _{DD}	—
LSYNC_IN	AJ10	I	OV _{DD}	—
	General Purpose I/O Timers			<u>ı</u>
GPIO1[0]/DMA_DREQ0/GTM1_TIN1/ GTM2_TIN2	F24	I/O	OV _{DD}	_
GPIO1[1]/DMA_DACK0/ GTM1_TGATE1/GTM2_TGATE2	E24	I/O	OV _{DD}	-

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TSEC2_TX_ER/GPIO1[24]	F14	I/O	OV _{DD}	—
TSEC2_TX_EN/GPIO1[12]	C5	I/O	LV _{DD2}	—
TSEC2_TX_CLK/GPIO1[30]	E14	I/O	OV _{DD}	—
	DUART			
UART_SOUT[1:2]/MSRCID[0:1]/ LSRCID[0:1]	AK27, AN29	0	OV _{DD}	—
UART_SIN[1:2]/MSRCID[2:3]/ LSRCID[2:3]	AL28, AM29	I/O	OV _{DD}	—
UART_CTS[1]/MSRCID4/LSRCID4	AP30	I/O	OV _{DD}	—
UART_CTS[2]/MDVAL/ LDVAL	AN30	I/O	OV _{DD}	—
UART_RTS[1:2]	AP31, AM30	0	OV _{DD}	—
	I ² C interface		•	
IIC1_SDA	AK29	I/O	OV _{DD}	2
IIC1_SCL	AP32	I/O	OV _{DD}	2
IIC2_SDA	AN31	I/O	OV _{DD}	2
IIC2_SCL	AM31	I/O	OV _{DD}	2
	SPI			
SPIMOSI/LCS[6]	AN32	I/O	OV _{DD}	_
SPIMISO/LCS[7]	AP33	I/O	OV _{DD}	_
SPICLK	AK30	I/O	OV _{DD}	_
SPISEL	AL31	I	OV _{DD}	_
	Clocks			
PCI_CLK_OUT[0:2]	AN9, AP9, AM10,	0	OV _{DD}	_
PCI_CLK_OUT[3]/LCS[6]	AN10	0	OV _{DD}	_
PCI_CLK_OUT[4]/LCS[7]	AJ11	0	OV _{DD}	_
PCI_CLK_OUT[5:7]	AP10, AL11, AM11	0	OV _{DD}	—
PCI_SYNC_IN/PCI_CLOCK	AK12	I	OV _{DD}	—
PCI_SYNC_OUT	AP11	0	OV _{DD}	3
RTC/PIT_CLOCK	AM32	I	OV _{DD}	_
CLKIN	AM9	I	OV _{DD}	_
	JTAG			
ТСК	E20	I	OV _{DD}	_
TDI	F20	I	OV _{DD}	4

Thermal

Heat sink vendors include the following list:	
Aavid Thermalloy 80 Commercial St. Concord, NH 03301 Internet: www.aavidthermalloy.com	603-224-9988
Alpha Novatech 473 Sapena Ct. #12 Santa Clara, CA 95054 Internet: www.alphanovatech.com	408-567-8082
International Electronic Research Corporation (IERC) 413 North Moss St. Burbank, CA 91502 Internet: www.ctscorp.com	818-842-7277
Millennium Electronics (MEI) Loroco Sites 671 East Brokaw Road San Jose, CA 95112 Internet: www.mei-thermal.com	408-436-8770
Tyco Electronics Chip Coolers [™] P.O. Box 3668 Harrisburg, PA 17105-3668 Internet: www.chipcoolers.com	800-522-2800
Wakefield Engineering 33 Bridge St. Pelham, NH 03076 Internet: www.wakefield.com	603-635-5102
Interface material vendors include the following:	
Chomerics, Inc. 77 Dragon Ct. Woburn, MA 01801 Internet: www.chomerics.com	781-935-4850
Dow-Corning Corporation Dow-Corning Electronic Materials P.O. Box 994 Midland, MI 48686-0997 Internet: www.dowcorning.com	800-248-2481
Shin-Etsu MicroSi, Inc. 10028 S. 51st St. Phoenix, AZ 85044 Internet: www.microsi.com	888-642-7674

800-347-4572

The Bergquist Company 18930 West 78th St. Chanhassen, MN 55317 Internet: www.bergquistcompany.com

20.3 Heat Sink Attachment

When heat sinks are attached, an interface material is required, preferably thermal grease and a spring clip. The spring clip should connect to the printed-circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces that can lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. The recommended maximum force on the top of the package is 10 lb force (4.5 kg force). Any adhesive attachment should attach to painted or plastic surfaces, and its performance should be verified under the application requirements.

20.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When a heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimize the size of the clearance to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

 T_J = junction temperature (°C) T_C = case temperature of the package (°C) $R_{\theta JC}$ = junction-to-case thermal resistance (°C/W) P_D = power dissipation (W)

21 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8349EA.

21.1 System Clocking

The MPC8349EA includes two PLLs:

1. The platform PLL generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in Section 19.1, "System PLL Configuration."

System Design Information

2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in Section 19.2, "Core PLL Configuration."

21.2 PLL Power Supply Filtering

Each PLL gets power through independent power supply pins ($AV_{DD}1$, $AV_{DD}2$, respectively). The AV_{DD} level should always equal to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme.

There are a number of ways to provide power reliably to the PLLs, but the recommended solution is to provide four independent filter circuits as illustrated in Figure 42, one to each of the four AV_{DD} pins. Independent filters to each PLL reduce the opportunity to cause noise injection from one PLL to the other.

The circuit filters noise in the PLL resonant frequency range from 500 kHz to 10 MHz. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

To minimize noise coupled from nearby circuits, each circuit should be placed as closely as possible to the specific AV_{DD} pin being supplied. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

Figure 42 shows the PLL power supply filter circuit.

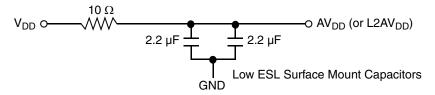


Figure 42. PLL Power Supply Filter Circuit

21.3 Decoupling Recommendations

Due to large address and data buses and high operating frequencies, the MPC8349EA can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8349EA system, and the device itself requires a clean, tightly regulated source of power. Therefore, the system designer should place at least one decoupling capacitor at each V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} pin of the device. These capacitors should receive their power from separate V_{DD} , OV_{DD} , GV_{DD} , LV_{DD} , and GND power planes in the PCB, with short traces to minimize inductance. Capacitors can be placed directly under the device using a standard escape pattern. Others can surround the part.

These capacitors should have a value of 0.01 or 0.1 μ F. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, distribute several bulk storage capacitors around the PCB, feeding the V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should

Rev. Number	Date	Substantive Change(s)
3	11/2006	 Updated note in introduction. In the features list in Section 1, "Overview," updated DDR data rate to show 400 MHz for DDR2 for TBGA parts for silicon 3.x and 400 MHz for DDR2 for TBGA parts for silicon 3.x. In Section 23, "Ordering Information," replicated note from document introduction.
2	8/2006	 Changed all references to revision 2.0 silicon to revision 3.0 silicon. Changed VIH minimum value in Table 40, "JTAG Interface DC Electrical Characteristics," to OV_{DD} - 0.3. In Table 44, "PCI DC Electrical Characteristics," changed high-level input voltage values to min = 2 and max = OV_{DD} + 0.3; changed low-level input voltage values to min = (-0.3) and max = 0.8. Updated DDR2 I/O power values in Table 5, "MPC8347EA Typical I/O Power Dissipation." In Table 66, "Suggested PLL Configurations," deleted reference-number rows 902 and 703.
1	4/2006	 Removed Table 20, "Timing Parameters for DDR2-400." Changed ADDR/CMD to ADDR/CMD/MODT in Table 9, "DDR and DDR2 SDRAM Output AC Timing Specifications," rows 2 and 3, and in Figure 2, "DDR SDRAM Output Timing Diagram. Changed Min and Max values for V_{IH} and VIL in Table 40Table 44,"PCI DC Electrical Characteristics." In Table 55, "MPC8349EA (TBGA) Pinout Listing," and Table 52, "MPC8347EA (PBGA) Pinout Listing," modified rows for MDICO and MDIC1 signals and added note 'It is recommended that MDICO be tied to GRD using an 18 Ω resistor and MCIC1 be tied to DDR power using an 18 Ω resistor.' Table 55, "MPC8349EA (TBGA) Pinout Listing," in row AVDD3 changed power supply from "AVDD3" to '—.'
0	3/2006	Initial public release

Table 68. Document Revision History (continued)

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